

width at its lower end, both of said lower layer and said upper layer having a larger band-gap than that of said active layer.

*C&R*  
*A2*

11. (Amended) A method of fabricating a semiconductor laser device, comprising the steps of:

forming a first semiconductor layer including an active layer; and  
forming a striped second semiconductor layer on said first semiconductor layer, and forming a current blocking layer on said first semiconductor layer on both sides of said semiconductor layer, the step of forming said second semiconductor layer comprising the step of forming a cladding layer which comprises a lower layer having a first width at its lower end and an upper layer having a second width larger than said first width at its lower end, both of said lower layer and said upper layer having a larger band-gap than that of said active layer.